

1. Description

BL30N60, the silicon N-channel Enhanced MOSFETs, is obtained by advanced MOSFET technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor is suitable device for SMPS, high speed switching and general purpose applications.

KEY CHARACTERISTICS

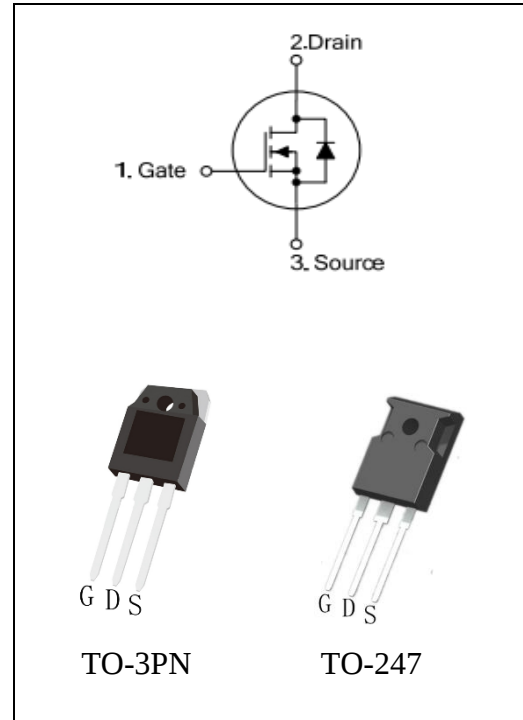
Parameter	Value	Unit
V_{DS}	600	V
I_D	30	A
$R_{DS(ON).Typ}$	0.12	Ω

FEATURES

- Fast Switching
- Low C_{rss}
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

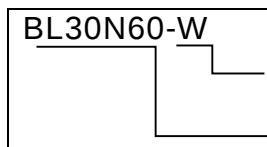
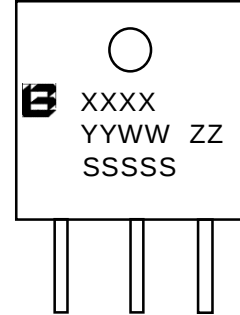
APPLICATIONS

- High frequency switching mode power supply
- Electronic ballast



ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
BL30N60-W	TO-3PN	30N60	Tube
BL30N60-F	TO-247		Tube

BL30N60-W  (2) Package type (1) Chip name (1) BL30N60: 600V 30A (2) W:TO-3PN F:TO-247	 XXXX: Product Code YYWW: Year&Week ZZ: Assembly Code SSSSS: Lot Code
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2. ABSOLUTE RATINGS

at $T_C = 25^{\circ}\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Units
V_{DS}	Drain-to-Source Voltage	600	V
I_D	Continuous Drain Current	30	A
	Continuous Drain Current $T_C = 100^{\circ}\text{C}$	19.8	A
I_{DM}	Pulsed Drain Current(Note1)	120	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulse Avalanche Energy(Note2)	3700	mJ
dv/dt	Peak Diode Recovery dv/dt (Note3)	5.0	V/ns
PD	Power Dissipation	365	W
	Derating Factor above 25°C	2.9	W/ $^{\circ}\text{C}$
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^{\circ}\text{C}$
T_L	Maximum Temperature for Soldering	300	$^{\circ}\text{C}$

3. Thermal characteristics

Thermal characteristics TO-3PN/TO-247

Symbol	Parameter	RATINGS	Units
$R_{\theta JC}$	Junction-to-Case	0.34	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient	62.5	$^{\circ}\text{C}/\text{W}$

4. Electrical Characteristics

 at $T_C = 25^\circ\text{C}$, unless otherwise specified

OFF Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	600	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	$I_D=250\mu A$, Reference 25°C	--	0.67	--	V/ $^\circ\text{C}$
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=600V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	--	--	1	μA
		$V_{DS}=480V$, $V_{GS}=0V$, $T_J=125^\circ\text{C}$	--	--	10	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+30V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-30V$	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V$, $I_D=15A$ (Note4)	--	0.12	0.15	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu A$ (Note4)	2	3	4	V
g_{fs}	Forward Transconductance	$V_{DS}=15V$, $I_D=15A$ (Note4)	--	52.0	--	S

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
R_g	Gate resistance	$f=1.0\text{MHz}$	--	1.1	--	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0\text{MHz}$	--	10000	--	PF
C_{oss}	Output Capacitance		--	640	--	
C_{rss}	Reverse Transfer Capacitance		--	28	--	

Switching Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	ID = 30A VDD = 300V VGS = 10V RG = 10 Ω	--	160	--	ns
t_r	Rise Time		--	550	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	125	--	
t_f	Fall Time		--	200	--	
Q_g	Total Gate Charge	ID = 30A VDD = 480V VGS = 10V	--	146	--	nC
Q_{gs}	Gate to Source Charge		--	50	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	32	--	

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)	TC=25 °C	--	--	30	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	120	A
V_{SD}	Diode Forward Voltage	IS=30A, VGS=0V(Note4)	--	--	1.2	V
T_{rr}	Reverse Recovery Time	IS=30A, Tj = 25°C dIF/dt=100A/us, VGS=0V	--	240	--	ns
Q_{rr}	Reverse Recovery Charge		--	6880	--	nC

Note1: Pulse width limited by maximum junction temperature

Note2: L=10mH, VDS=200V, Rg=25 Ω , Start TJ=25°C

Note3: ISD =30A, di/dt $\leq$ 100A/us, VDD $\leq$ BVDS, Start TJ=25°C

Note4: Pulse width tp $\leq$ 300 μ s, δ $\leq$ 2%

5. Characteristics Curves

Figure 1 Safe Operating Area

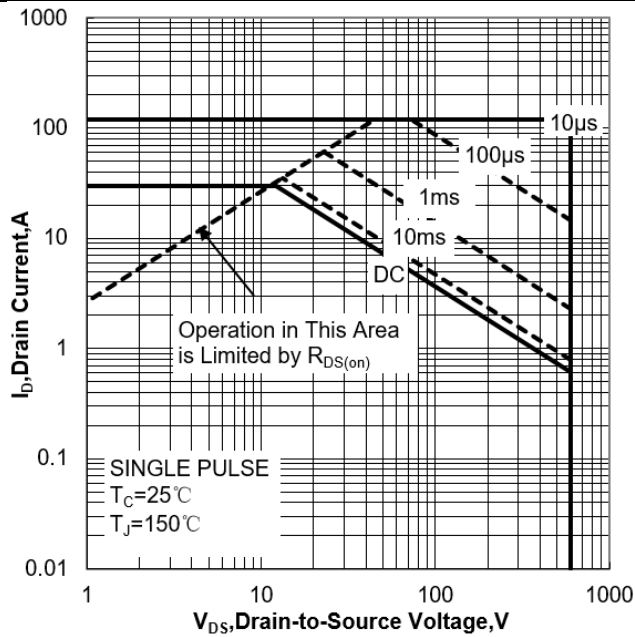


Figure 2 Power Dissipation

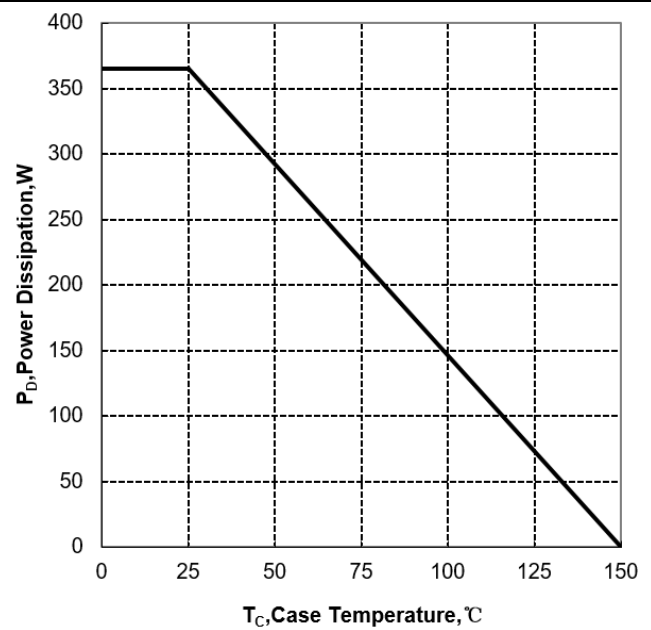


Figure 3 Max Thermal Impedance

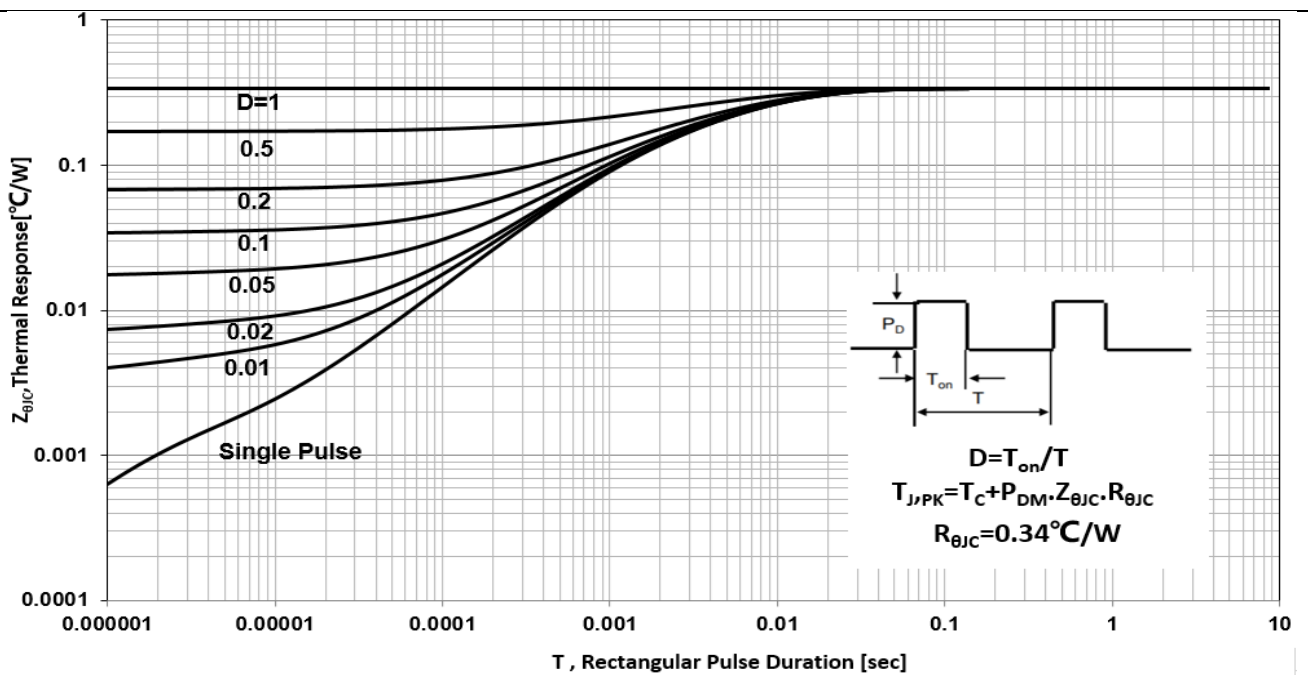


Figure 4 Typical Output Characteristics

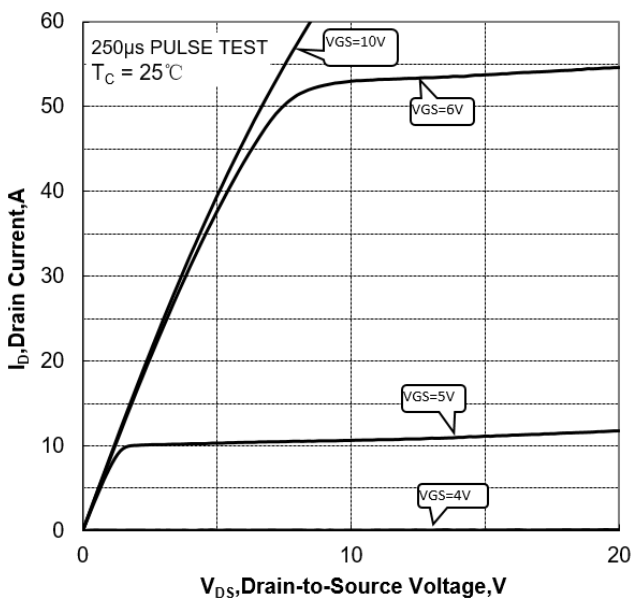


Figure 5 Typical Transfer Characteristics

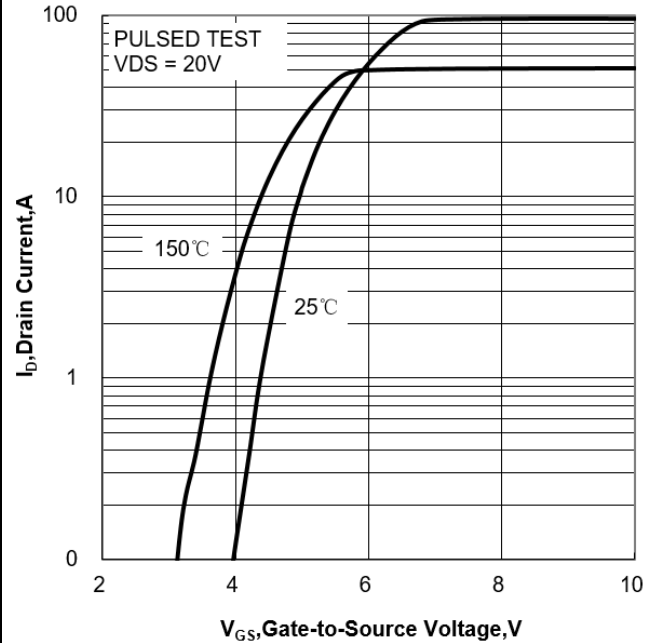


Figure 6 Typical Drain to Source ON Resistance vs Drain Current

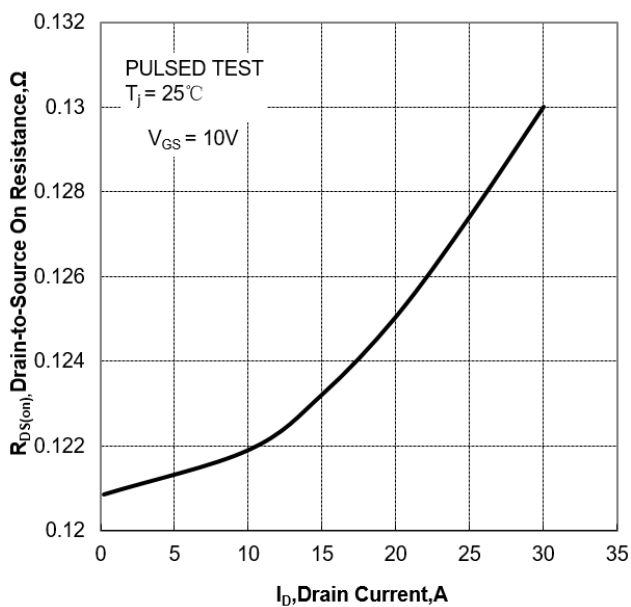


Figure 7 Typical Drain to Source on Resistance vs Junction Temperature

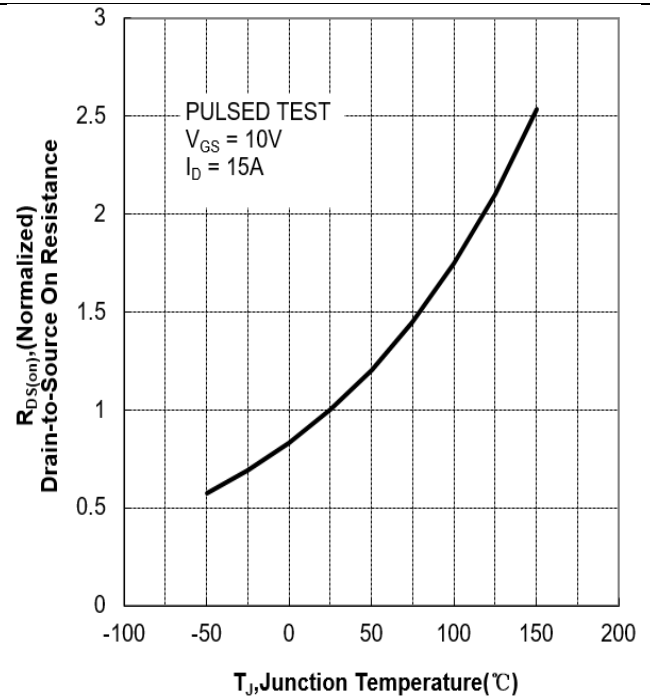


Figure 8 Typical Theshold Voltage vs Junction Temperature

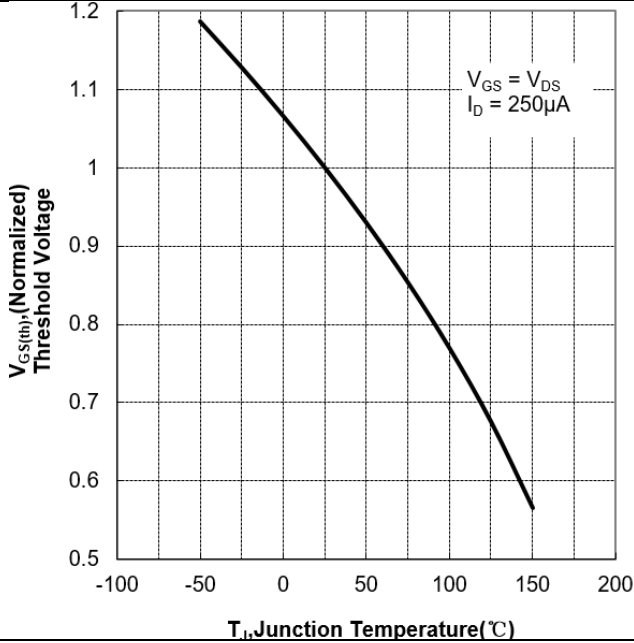


Figure 9 Typical Breakdown Voltage vs Junction Temperature

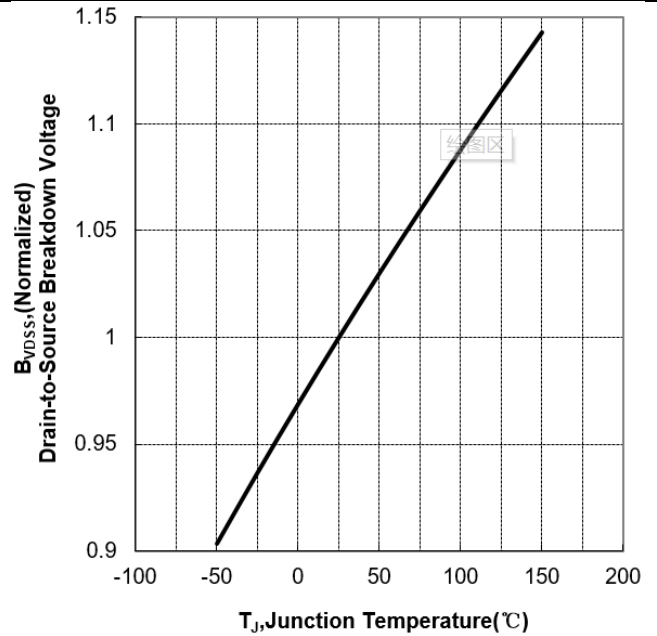


Figure 10 Typical Capacitance vs Drain to Source Voltage

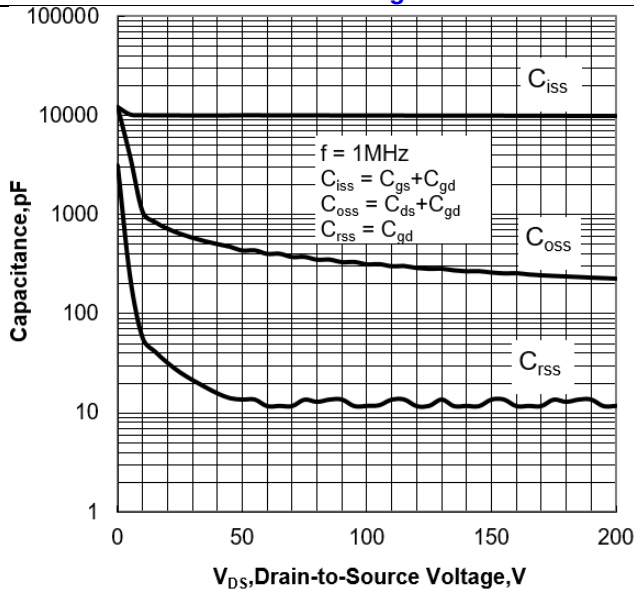
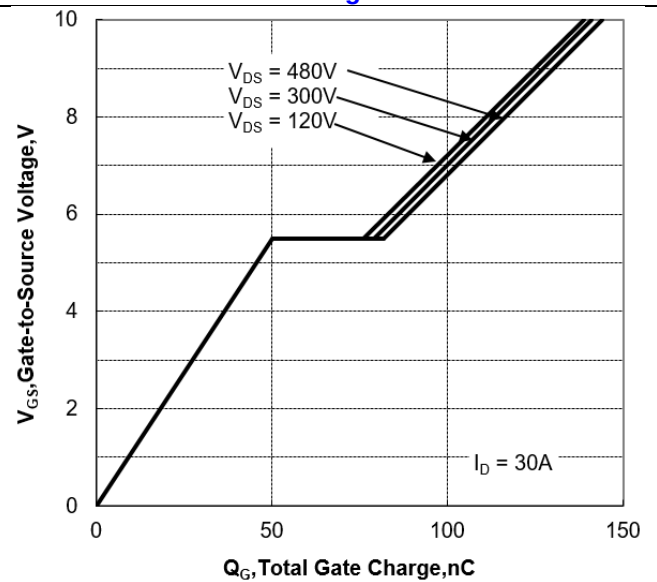
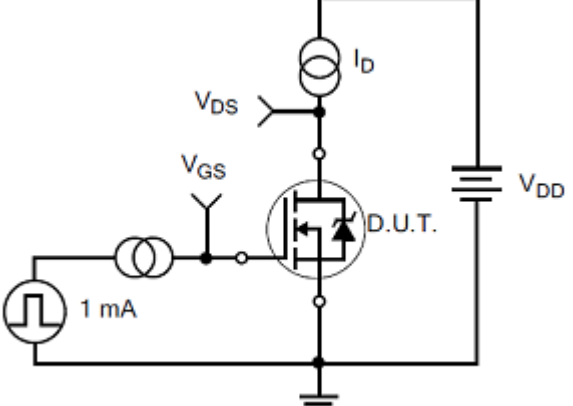
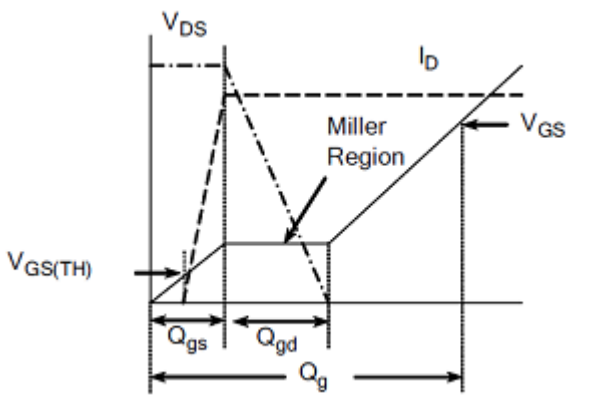
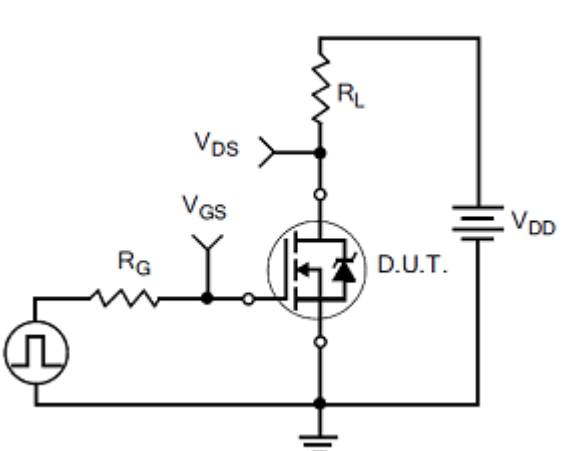
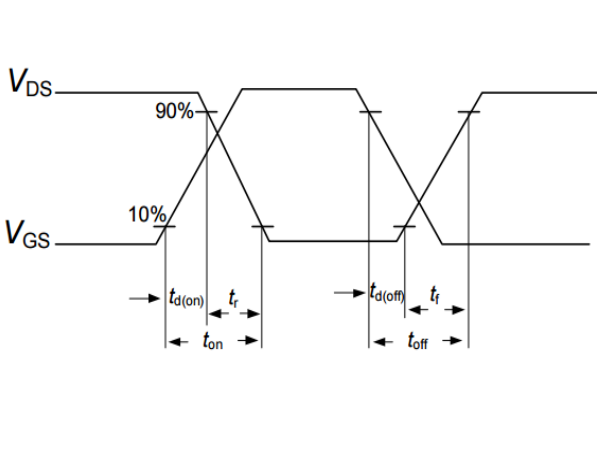


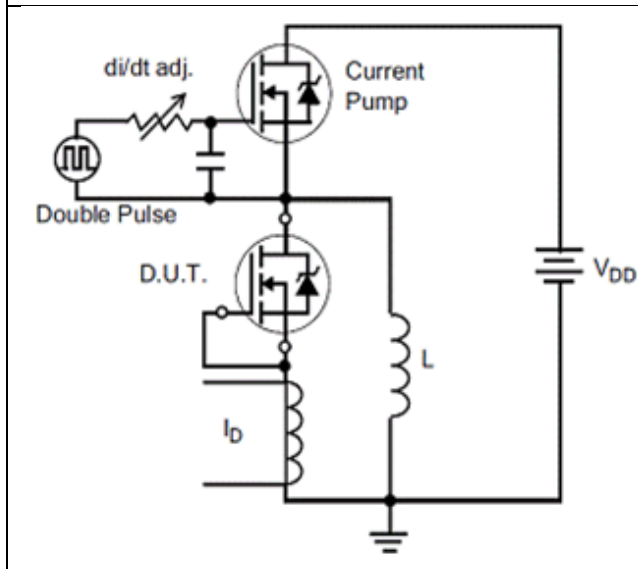
Figure 11 Typical Gate Charge vs Gate to Source Voltage



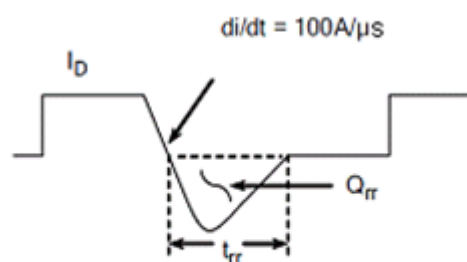
6. Test Circuit and Waveform

Gate Charge Test Circuit	Gate Charge Waveforms
 The diagram shows a MOSFET (D.U.T.) in a common-source configuration. The gate is driven by a 1 mA current source. The drain is connected to a load resistor and a drain current source I_D. The gate-source voltage is V_{GS} and the drain-source voltage is V_{DS}. The supply voltage is V_{DD}.	 The diagram shows the relationship between V_{DS}, I_D, and V_{GS} during a gate charge test. The Miller Region is indicated. Key parameters shown are $V_{GS(TH)}$, Q_{gs}, Q_{gd}, and Q_g.
Resistive Switching Test Circuit	Resistive Switching Waveforms
 The diagram shows a MOSFET (D.U.T.) in a common-source configuration. The gate is driven by a current source through a gate resistor R_G. The drain is connected to a load resistor R_L and the supply voltage V_{DD}. The gate-source voltage is V_{GS} and the drain-source voltage is V_{DS}.	 The diagram shows the switching waveforms for V_{DS} and V_{GS}. Key parameters shown are $t_{d(on)}$, t_r, t_{on}, $t_{d(off)}$, t_f, and t_{off}.

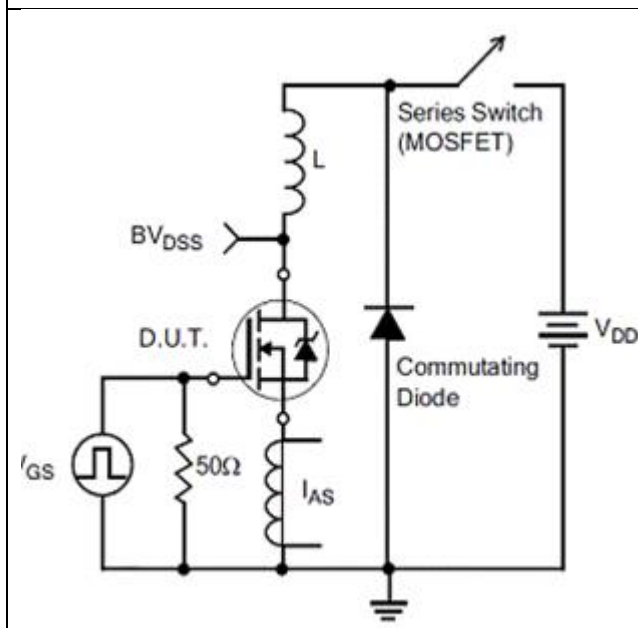
Diode Reverse Recovery Test Circuit



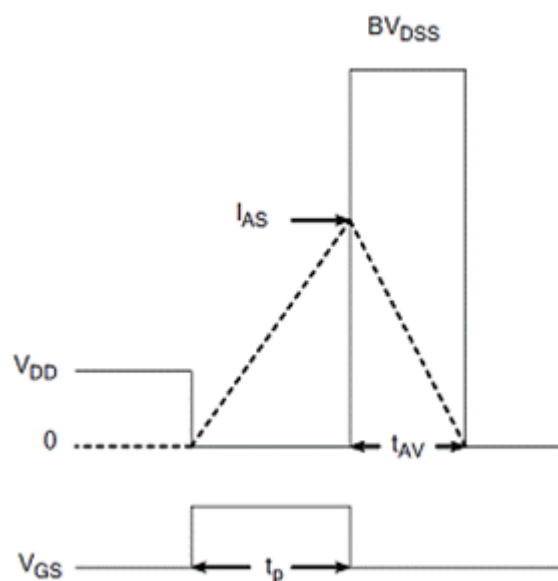
Diode Reverse Recovery Waveform



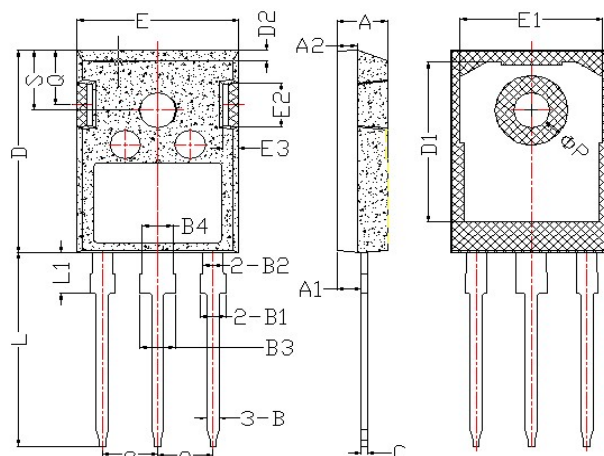
Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveform

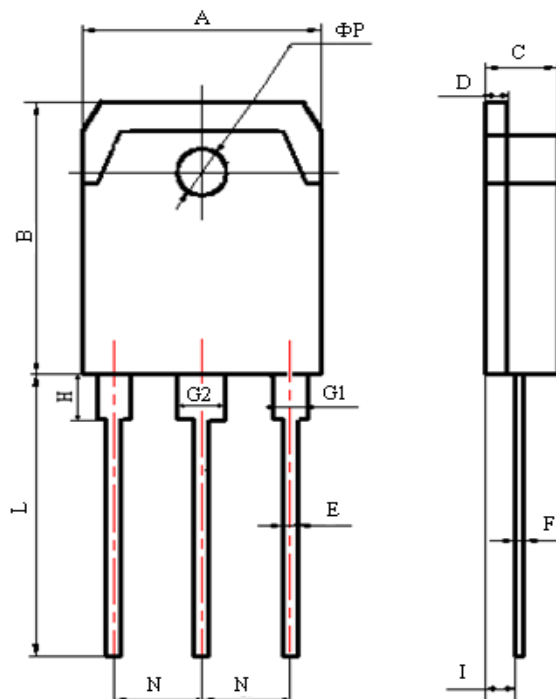


7. Package Description



Items	Values(mm)	
	MIN	MAX
A	4.6	5.2
A1	2.2	2.6
B	0.9	1.4
B1	1.75	2.35
B2	1.75	2.15
B3	2.8	3.35
B4	2.8	3.15
C	0.5	0.7
D	20.60	21.30
D1	16	18
E	15.5	16.10
E1	13	14.7
E2	3.80	5.3
E3	0.8	2.60
e	5.2	5.7
L	19	20.5
L1	3.9	4.6
Φ _P	2.5	3.70
Q	5.2	6.00
S	5.8	6.6

TO-247 Package



Items	Values(mm)	
	MIN	MAX
A	15.00	16.00
B	19.20	20.60
C	4.60	5.00
D	1.40	1.60
E	0.90	1.10
F	0.50	0.70
G1	2.00	2.20
G2	3.00	3.20
H	3.00	3.70
I	1.20	1.70
	2.70	2.90
L	19.00	21.00
N	5.25	5.65
Φ P	3.10	3.30

TO-3PN Package

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shanghai Belling reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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